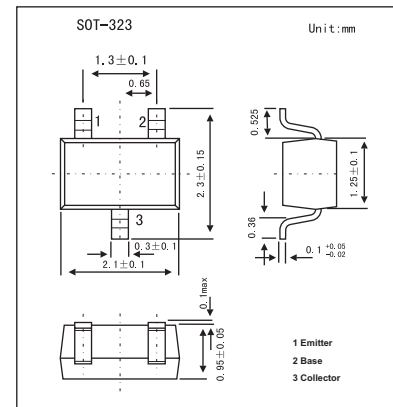
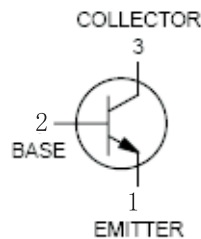


General Purpose Transistor

MMBT2222AW

■ Features

- General purpose transistor.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-emitter voltage	V _{CEO}	40	V
Collector-base voltage	V _{CB0}	75	V
Emitter-base voltage	V _{EB0}	6.0	V
Collector current	I _C	600	mA
Total Device Dissipation FR-5 Board	P _D	150	mW
Thermal Resistance, Junction-to-Ambient	R _{θJA}	833	°C/W
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

MMBT2222AW

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1.0\text{ mA}, I_B = 0$	40			V
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\text{ }\mu\text{A}, I_E = 0$	75			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\text{ }\mu\text{A}, I_C = 0$	6			V
Base cutoff current	I_{BL}	$V_{CE} = 60\text{ V}, V_{EB} = 3.0\text{ V}$			20	nA
Collector cutoff current	I_{CEX}	$V_{CE} = 60\text{ V}, V_{EB} = 3.0\text{ V}$			10	nA
DC current gain *	H_{FE}	$I_C = 150\text{ mA}, V_{CE} = 10\text{ V}$	100		300	
Collector-emitter saturation voltage *	$V_{CE(sat)}$	$I_C = 150\text{ mA}, I_B = 15\text{ mA}$			0.3	V
		$I_C = 500\text{ mA}, I_B = 50\text{ mA}$			1.0	
Base-emitter saturation voltage *	$V_{BE(sat)}$	$I_C = 150\text{ mA}, I_B = 15\text{ mA}$	0.6		1.2	
		$I_C = 500\text{ mA}, I_B = 50\text{ mA}$			2.0	
Current-gain-bandwidth product	f_T	$I_C = 20\text{ mA}, V_{CE} = 20\text{ V}, f = 100\text{ MHz}$	300			MHz
Output capacitance	C_{obo}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1.0\text{ MHz}$			8.0	pF
Input capacitance	C_{ibo}	$V_{EB} = 0.5\text{ V}, I_C = 0, f = 1.0\text{ MHz}$			30	pF
Input impedance	h_{ie}	$V_{CE} = 10\text{ V}, I_C = 10\text{ mA}, f = 1.0\text{ kHz}$	0.25		1.25	k Ω
Voltage feedback ratio	h_{re}	$V_{CE} = 10\text{ V}, I_C = 10\text{ mA}, f = 1.0\text{ kHz}$			4.0	$\times 10^{-4}$
Small-signal current gain	h_{fe}	$V_{CE} = 10\text{ V}, I_C = 10\text{ mA}, f = 1.0\text{ kHz}$	75		375	
Output admittance	h_{oe}	$V_{CE} = 10\text{ V}, I_C = 10\text{ mA}, f = 1.0\text{ kHz}$	25		200	μmhos
Noise figure	NF	$V_{CE} = 10\text{ V}, I_C = 100\text{ }\mu\text{A}, R_s = 1.0\text{ k}\Omega, f = 1.0\text{ kHz}$			4.0	dB
Delay time	t_d	$V_{CC} = 3.0\text{ V}, V_{BE} = -0.5\text{ V}, I_C = 150\text{ mA}, I_{B1} = 15\text{ mA}$			10	ns
Rise time	t_r				25	ns
Storage time	t_s	$V_{CC} = 30\text{ V}, I_C = 150\text{ mA}, I_{B1} = I_{B2} = 15\text{ mA}$			225	ns
Fall time	t_f				60	ns

* Pulse test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2.0\%$.

■ Marking

Marking	P1
---------	----